

ABSTRACT OF THE DISCLOSURE

A method is provided, the method comprising monitoring consumption of a sputter target to determine a deposition rate of a metal layer during metal deposition processing using the sputter target, and modeling a dependence of the deposition rate on at least one of
5 deposition plasma power and deposition time. The method also comprises applying the deposition rate model to modify the metal deposition processing to form the metal layer to have a desired thickness.

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